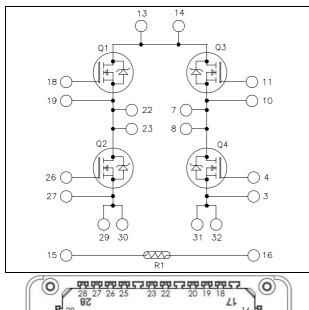
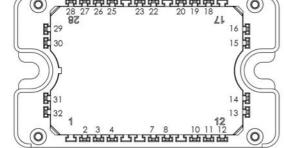


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Full bridge MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

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 $V_{DSS} = 1000V$

 $R_{DSon} = 460 m\Omega \text{ typ}$ (a) $Tj = 25^{\circ}C$

$I_D = 19A$ (a) $T_c = 25^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 8TM Fast FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|-------------------|---|---------------------|-------------|------|
| V _{DSS} | Drain - Source Voltage | | 1000 | V |
| т | Continuous Duoin Cumont | $T_c = 25^{\circ}C$ | 19 | |
| ID | Continuous Drain Current | $T_c = 80^{\circ}C$ | 14 | А |
| I _{DM} | Pulsed Drain current | | | |
| V _{GS} | Gate - Source Voltage | | ± 30 | V |
| R _{DSon} | Drain - Source ON Resistance | | 552 | mΩ |
| PD | Power Dissipation | $T_c = 25^{\circ}C$ | 357 | W |
| I _{AR} | Avalanche current (repetitive and non repetitive) | | 16 | А |

🕅 A CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------|--|-----|-----|------|------|
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 1000V$; $V_{GS} = 0V$ | | | 250 | μA |
| R _{DS(on)} | Drain – Source on Resistance | $V_{GS} = 10V, I_D = 16A$ | | 460 | 552 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$ | 3 | 4 | 5 | V |
| I _{GSS} | Gate – Source Leakage Current | $V_{GS} = \pm 30 \text{ V}$ | | | ±150 | nA |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Тур | Max | Unit |
|--------------------|------------------------------------|--|-----|------|------|------|
| Ciss | Input Capacitance | $V_{GS} = 0V$ | | 6800 | | |
| Coss | Output Capacitance | $V_{DS} = 25V$ | | 715 | | pF |
| C _{rss} | Reverse Transfer Capacitance | f = 1MHz | | 92 | | |
| Q_{g} | Total gate Charge | $V_{GS} = 10V$ | | 260 | | |
| Q_{gs} | Gate – Source Charge | $V_{Bus} = 500V$ | | 46 | | nC |
| Q_{gd} | Gate – Drain Charge | $I_D = 16A$ | | 125 | | |
| T _{d(on)} | Turn-on Delay Time | $\label{eq:constraint} \begin{array}{l} \mbox{Resistive switching @ 25°C} \\ V_{GS} = 15V \\ V_{Bus} = 667V \\ I_D = 16A \\ R_G = 2.2\Omega \end{array}$ | | 36 | | |
| Tr | Rise Time | | | 37 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 140 | | ns |
| T_{f} | Fall Time | | | 35 | | |
| R _{thJC} | Junction to Case Thermal Resistanc | e | | | 0.35 | °C/W |

Source - Drain diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|-----------------|------------------------------|---|----------------------|-----|-----|-----|------|
| т | Continuous Source current | | $Tc = 25^{\circ}C$ | | | 19 | А |
| Is | (Body diode) | | $Tc = 80^{\circ}C$ | | | 14 | А |
| V _{SD} | Diode Forward Voltage | $V_{GS} = 0V, I_S = -16A$ | | | | 1 | V |
| dv/dt | Peak Diode Recovery 1 | | | | | 25 | V/ns |
| t _{rr} | | | $T_j = 25^{\circ}C$ | | | 290 | |
| | Reverse Recovery Time | $I_{\rm S} = -16A$ $V_{\rm R} = 100V$ | $T_j = 125^{\circ}C$ | | | 600 | ns |
| Q _{rr} | Reverse Recovery Charge | $v_{\rm R} = 100 v$ dis/dt = 100A/µs | $T_j = 25^{\circ}C$ | | 1.3 | | μC |
| | | | $T_j = 125^{\circ}C$ | | 3.5 | | μ |

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{-} \ 16A \qquad di/dt \leq 1000 A/\mu s \qquad V_{DD} \leq 667V \qquad T_j \leq 125^\circ C$



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Thermal and package characteristics

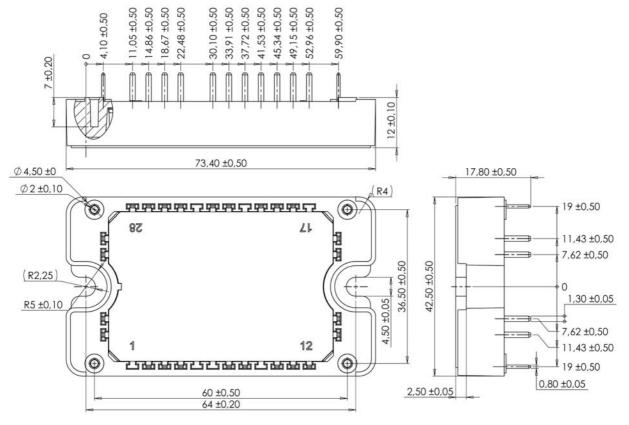
| Symbol | Characteristic | | | Min | Max | Unit |
|------------------|---|-------------|----|-----|-------------------------|------|
| VISOL | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | | | | V |
| TJ | Operating junction temperature range | | | -40 | 150 | |
| T _{JOP} | Recommended junction temperature under switching conditions | | | -40 | T _J max - 25 | °C |
| T _{STG} | Storage Temperature Range | | | -40 | 125 | C |
| T _C | Operating Case Temperature | | | -40 | 125 | |
| Torque | Mounting torque | To heatsink | M4 | 2 | 3 | N.m |
| Wt | Package Weight | | | | 110 | g |

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | | Min | Тур | Max | Unit |
|------------------------|-----------------------------|-----------------------|-----|------|-----|------|
| R ₂₅ | Resistance @ 25°C | | | 50 | | kΩ |
| $\Delta R_{25}/R_{25}$ | | | | 5 | | % |
| B _{25/85} | $T_{25} = 298.15 \text{ K}$ | | | 3952 | | K |
| $\Delta B/B$ | | T _C =100°C | | 4 | | % |

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

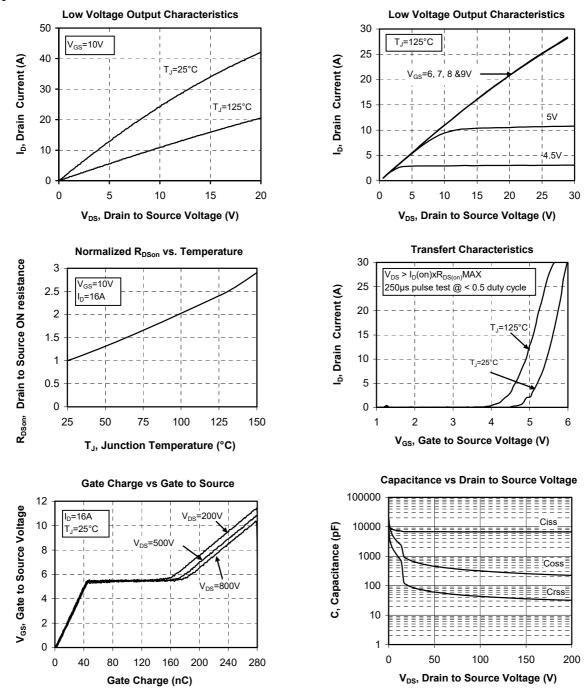
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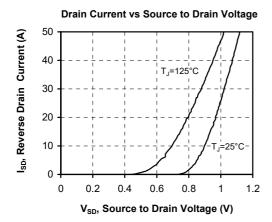
Typical Performance Curve

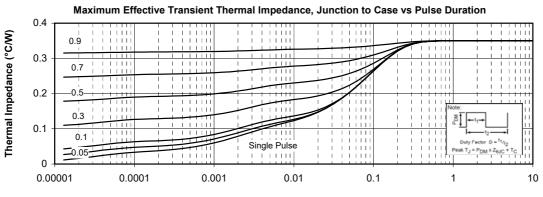


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rectangular Pulse Duration (Seconds)



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